

**FEATURES**

- Double Side Cooling
- High Surge Capability

**APPLICATIONS**

- High Power Drives
- High Voltage Power Supplies
- Static Switches

**VOLTAGE RATINGS**

Part and Ordering Number	Repetitive Peak Voltages $V_{DRM}$ and $V_{RRM}$ V	Conditions
DCR2930Y42	4200	$T_{vj} = -40^{\circ}\text{C}$ to $125^{\circ}\text{C}$ , $I_{DRM} = I_{RRM} = 200\text{mA}$ , $V_{DRM}, V_{RRM} t_p = 10\text{ms}$ , $V_{DSM} \& V_{RSM} =$ $V_{DRM} \& V_{RRM} + 100\text{V}$ respectively
DCR2930Y40	4000	
DCR2930Y35	3500	
DCR2930Y30	3000	

Lower voltage grades available.

**ORDERING INFORMATION**

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

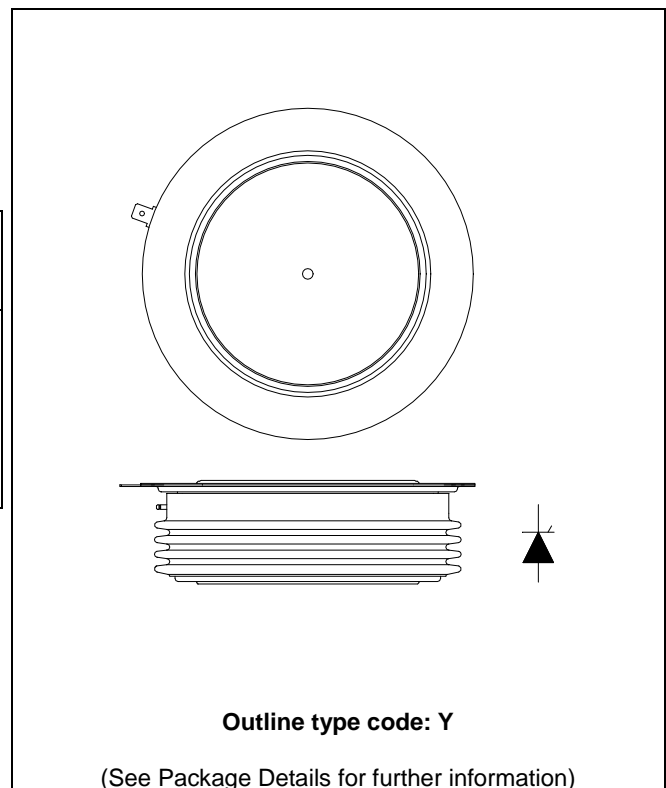
**DCR2930Y42**

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

**KEY PARAMETERS**

$V_{DRM}$	<b>4200V</b>
$I_{T(AV)}$	<b>2930A</b>
$I_{TSM}$	<b>40600A</b>
$dV/dt^*$	<b>1500V/<math>\mu\text{s}</math></b>
$di/dt$	<b>400A/<math>\mu\text{s}</math></b>

\* Higher  $dV/dt$  selections available



**Fig. 1 Package outline**

## CURRENT RATINGS

$T_{case} = 60^{\circ}\text{C}$  unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
<b>Double Side Cooled</b>				
$I_{T(AV)}$	Mean on-state current	Half wave resistive load	2930	A
$I_{T(RMS)}$	RMS value	-	4600	A
$I_T$	Continuous (direct) on-state current	-	4210	A

## SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
$I_{TSM}$	Surge (non-repetitive) on-state current	10ms half sine, $T_{case} = 125^{\circ}\text{C}$	40.6	kA
$I^2t$	$I^2t$ for fusing	$V_R = 0$	8.24	$\text{MA}^2\text{s}$

## THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions	Min.	Max.	Units	
$R_{th(j-c)}$	Thermal resistance – junction to case	Double side cooled	DC	-	0.00835	$^{\circ}\text{C/W}$
		Single side cooled	Anode DC	-	0.0134	$^{\circ}\text{C/W}$
			Cathode DC	-	0.023	$^{\circ}\text{C/W}$
$R_{th(c-h)}$	Thermal resistance – case to heatsink	Clamping force 54.0kN (with mounting compound)	Double side	-	0.002	$^{\circ}\text{C/W}$
			Single side	-	0.004	$^{\circ}\text{C/W}$
$T_{vj}$	Virtual junction temperature	Blocking $V_{DRM} / V_{RRM}$	-	125	$^{\circ}\text{C}$	
$T_{stg}$	Storage temperature range		-55	125	$^{\circ}\text{C}$	
$F_m$	Clamping force		48	59	kN	

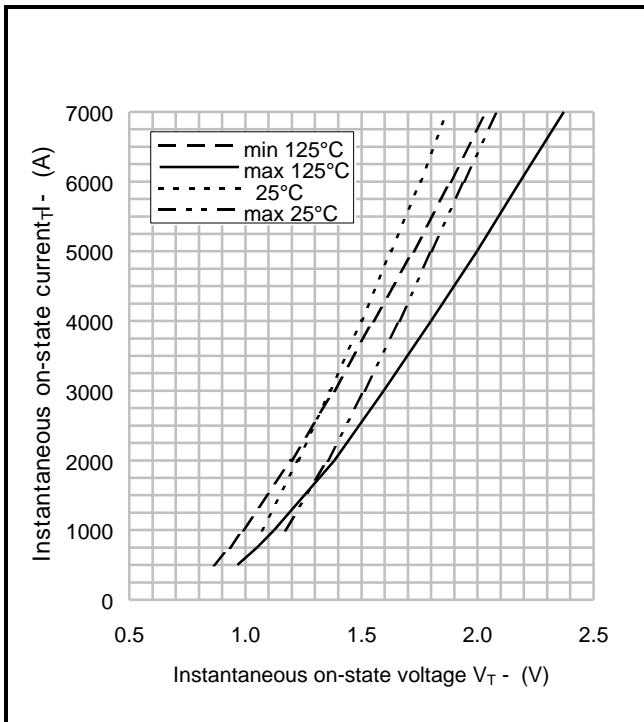
**DYNAMIC CHARACTERISTICS**

Symbol	Parameter	Test Conditions	Min.	Max.	Units	
$I_{RRM}/I_{DRM}$	Peak reverse and off-state current	At $V_{RRM}/V_{DRM}$ , $T_{case} = 125^{\circ}C$	-	200	mA	
$dV/dt$	Max. linear rate of rise of off-state voltage	To 67% $V_{DRM}$ , $T_j = 125^{\circ}C$ , gate open	-	1500	V/ $\mu s$	
$di/dt$	Rate of rise of on-state current	From 67% $V_{DRM}$ to $2x I_{T(AV)}$	Repetitive 50Hz	-	150	A/ $\mu s$
		Gate source 30V, 10 $\Omega$ , $t_r < 0.5\mu s$ , $T_j = 125^{\circ}C$	Non-repetitive	-	400	A/ $\mu s$
$V_{T(TO)}$	Threshold voltage – Low level	500A to 3000A at $T_{case} = 125^{\circ}C$	-	0.82	V	
	Threshold voltage – High level	3000A to 7200A at $T_{case} = 125^{\circ}C$	-	0.98	V	
$r_T$	On-state slope resistance – Low level	500A to 3000A at $T_{case} = 125^{\circ}C$	-	0.292	m $\Omega$	
	On-state slope resistance – High level	3000A to 7200A at $T_{case} = 125^{\circ}C$	-	0.198	m $\Omega$	
$t_{gd}$	Delay time	$V_D = 67\% V_{DRM}$ , gate source 30V, 10 $\Omega$ $t_r = 0.5\mu s$ , $T_j = 25^{\circ}C$	TBD	TBD	$\mu s$	
$t_q$	Turn-off time	$T_j = 125^{\circ}C$ , $V_R = 200V$ , $di/dt = 1A/\mu s$ , $dV_{DR}/dt = 20V/\mu s$ linear	250	500	$\mu s$	
$Q_S$	Stored charge	$I_T = 2000A$ , $T_j = 125^{\circ}C$ , $di/dt = 1A/\mu s$ ,	1200	3500	$\mu C$	
$I_L$	Latching current	$T_j = 25^{\circ}C$ , $V_D = 5V$	-	3	A	
$I_H$	Holding current	$T_j = 25^{\circ}C$ , $R_{G-K} = \infty$ , $I_{TM} = 500A$ , $I_T = 5A$	-	300	mA	

**GATE TRIGGER CHARACTERISTICS AND RATINGS**

Symbol	Parameter	Test Conditions	Max.	Units
V <sub>GT</sub>	Gate trigger voltage	V <sub>DRM</sub> = 5V, T <sub>case</sub> = 25°C	1.5	V
V <sub>GD</sub>	Gate non-trigger voltage	At V <sub>DRM</sub> , T <sub>case</sub> = 125°C	TBD	V
I <sub>GT</sub>	Gate trigger current	V <sub>DRM</sub> = 5V, T <sub>case</sub> = 25°C	350	mA
I <sub>GD</sub>	Gate non-trigger current	V <sub>DRM</sub> = 5V, T <sub>case</sub> = 25°C	TBD	mA

**CURVES**



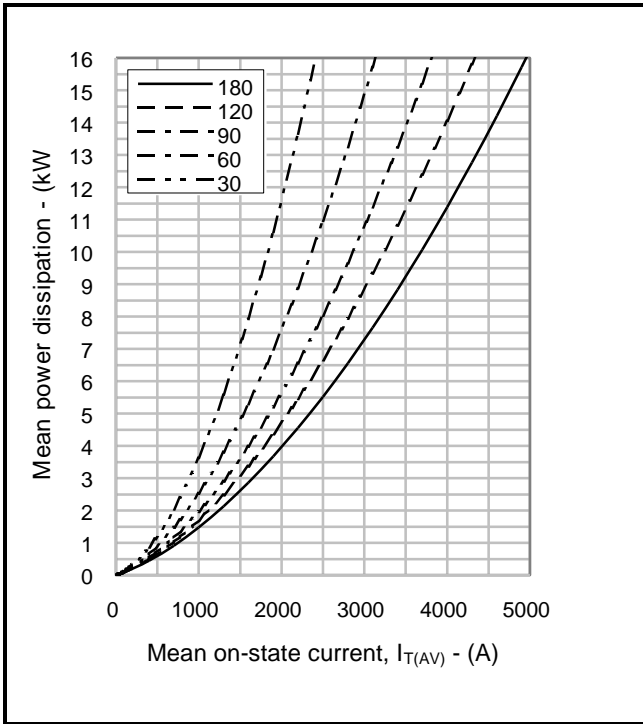
**Fig.2 Maximum & minimum on-state characteristics**

**V<sub>TM</sub> EQUATION**

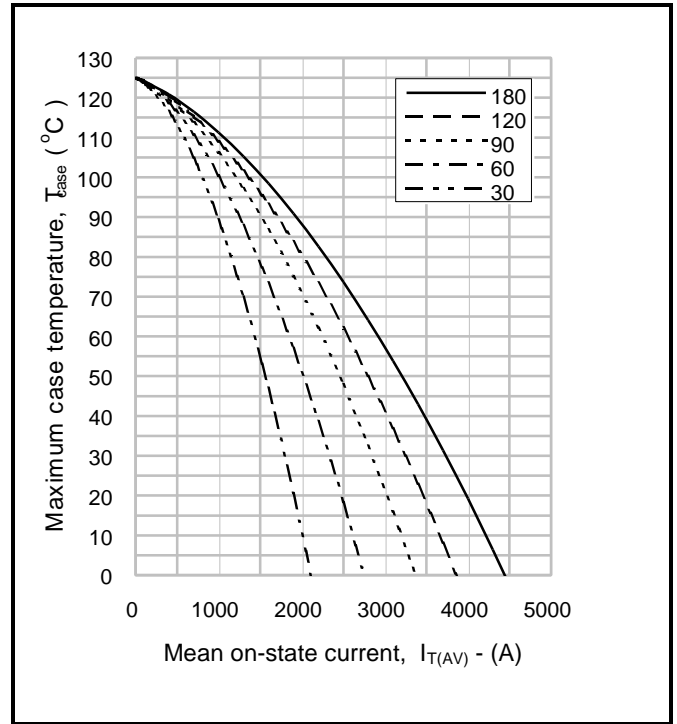
$$V_{TM} = A + B \ln(I_T) + C \cdot I_T + D \cdot \sqrt{I_T}$$

Where A = 0.866995  
 B = -0.042053  
 C = 0.000100  
 D = 0.014062

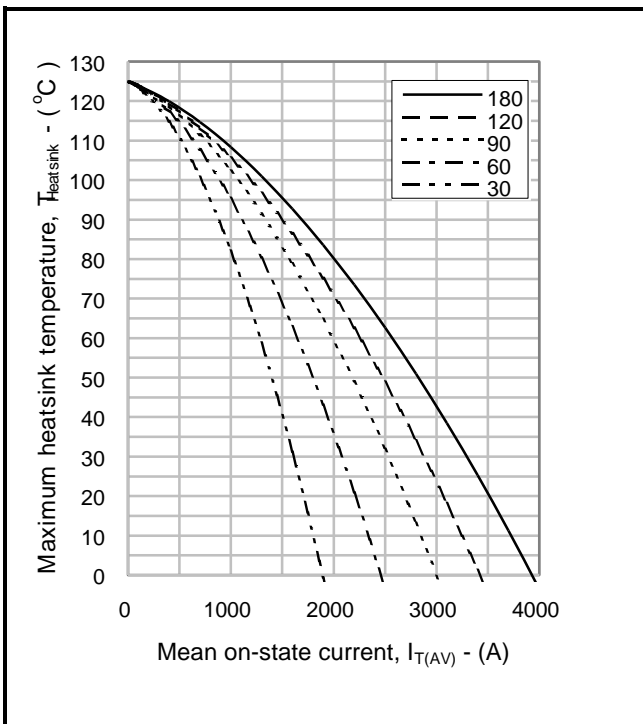
these values are valid for T<sub>j</sub> = 125°C for I<sub>T</sub> 500A to 10,000A



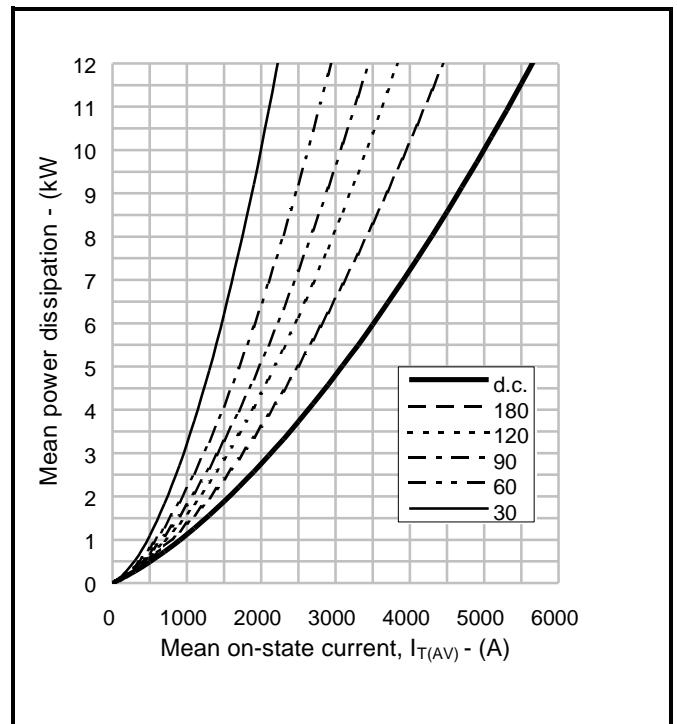
**Fig.3 On-state power dissipation – sine wave**



**Fig.4 Maximum permissible case temperature, double side cooled – sine wave**



**Fig.5 Maximum permissible heatsink temperature, double side cooled – sine wave**



**Fig.6 On-state power dissipation – rectangular wave**

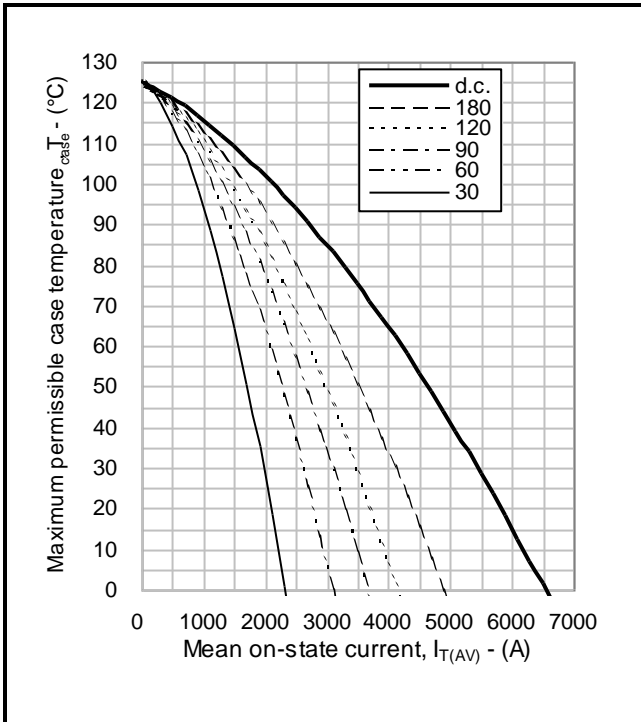


Fig.7 Maximum permissible case temperature, double side cooled – rectangular wave

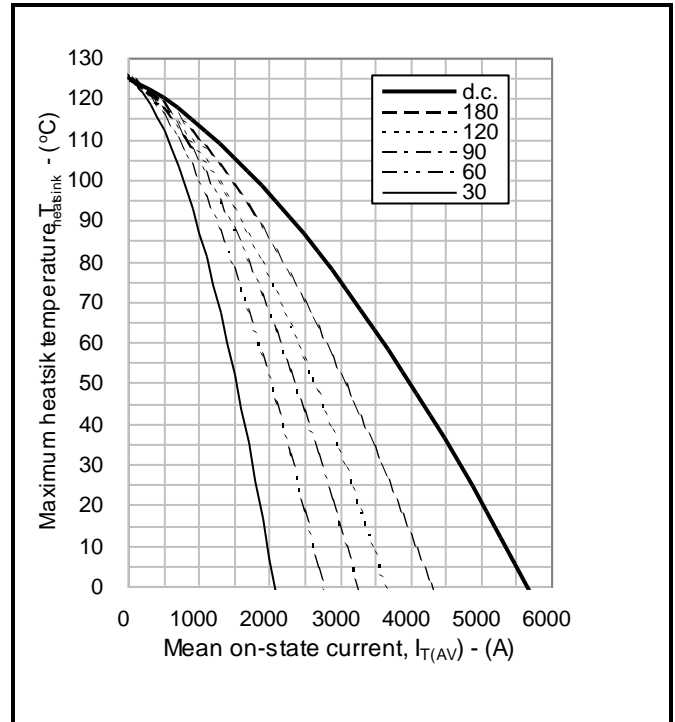


Fig.8 Maximum permissible heatsink temperature, double side cooled – rectangular wave

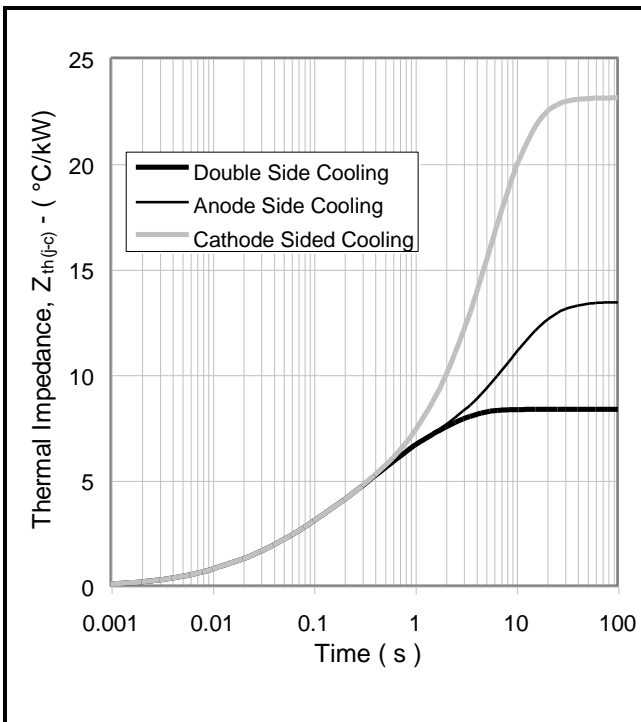


Fig.9 Maximum (limit) transient thermal impedance – junction to case (°C/kW)

		1	2	3	4
Double side cooled	$R_i$ (°C/kW)	0.612	1.7721	3.1053	2.8608
	$T_i$ (s)	0.010332	0.056415	0.333082	1.6323
Anode side cooled	$R_i$ (°C/kW)	0.7009	1.9388	3.61	7.1383
	$T_i$ (s)	0.011328	0.065993	0.419695	9.0612
Cathode side cooled	$R_i$ (°C/kW)	0.6728	2.0168	1.7306	18.6391
	$T_i$ (s)	0.010954	0.065544	0.30379	5.7274

$$Z_{th} = \sum [R_i \times (1 - \exp. (-t/t_i))] \quad [1]$$

$\Delta R_{th(j-c)}$  Conduction

Tables show the increments of thermal resistance  $R_{th(j-c)}$  when the device operates at conduction angles other than d.c.

Double side cooling			Anode Side Cooling			Cathode Sided Cooling		
$\theta^\circ$	$\Delta Z_{th} (z)$		$\theta^\circ$	$\Delta Z_{th} (z)$		$\theta^\circ$	$\Delta Z_{th} (z)$	
	sine.	rect.		sine.	rect.		sine.	rect.
180	0.94	0.65	180	0.94	0.64	180	0.94	0.64
120	1.09	0.92	120	1.08	0.91	120	1.08	0.91
90	1.24	1.07	90	1.23	1.06	90	1.24	1.06
60	1.38	1.23	60	1.37	1.22	60	1.37	1.22
30	1.49	1.40	30	1.47	1.38	30	1.48	1.39
15	1.54	1.49	15	1.52	1.47	15	1.53	1.48

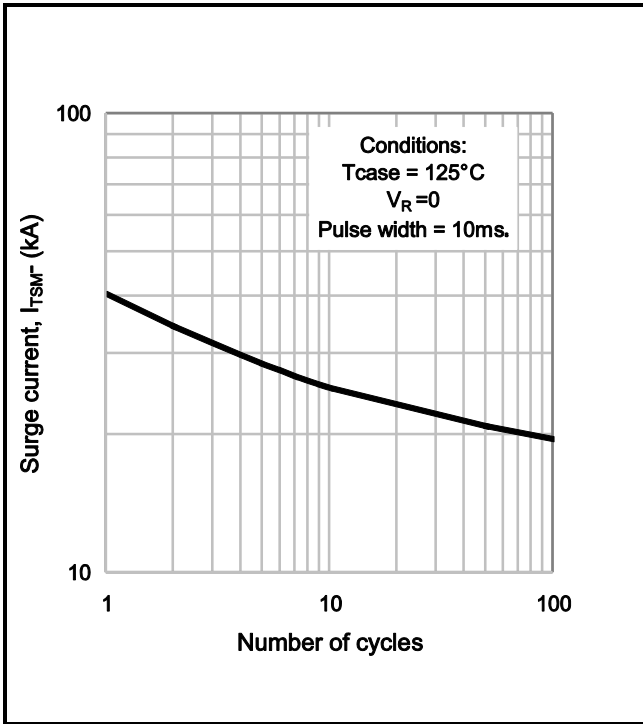


Fig.10 Multi-cycle surge current

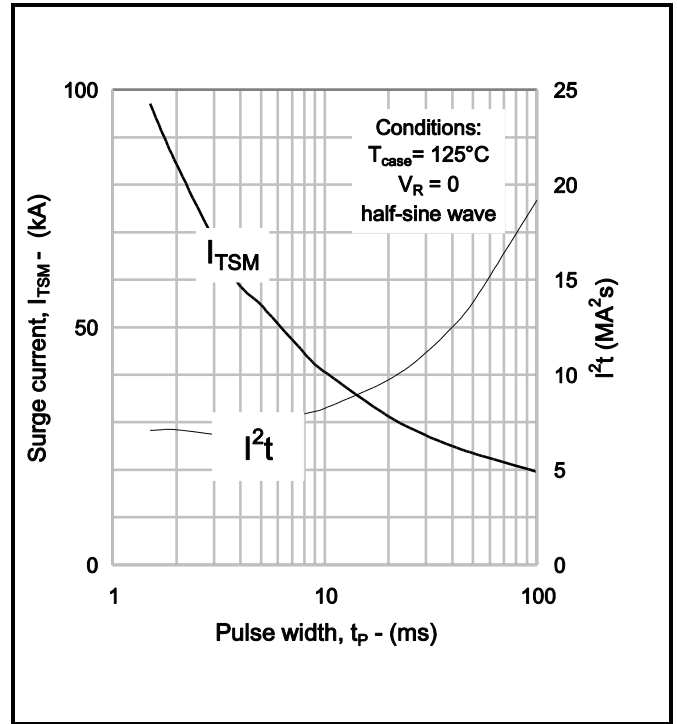


Fig.11 Single-cycle surge current

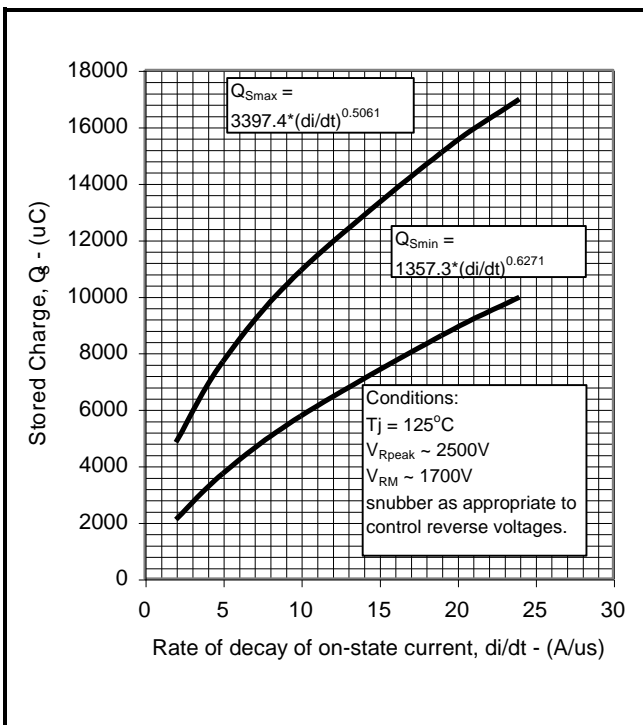


Fig.12 Stored Charge

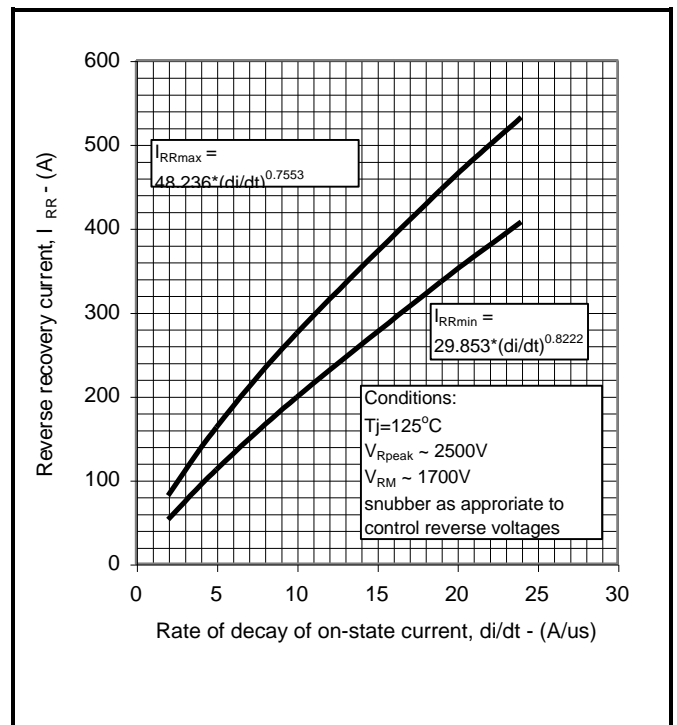


Fig.13 Reverse Recovery Current

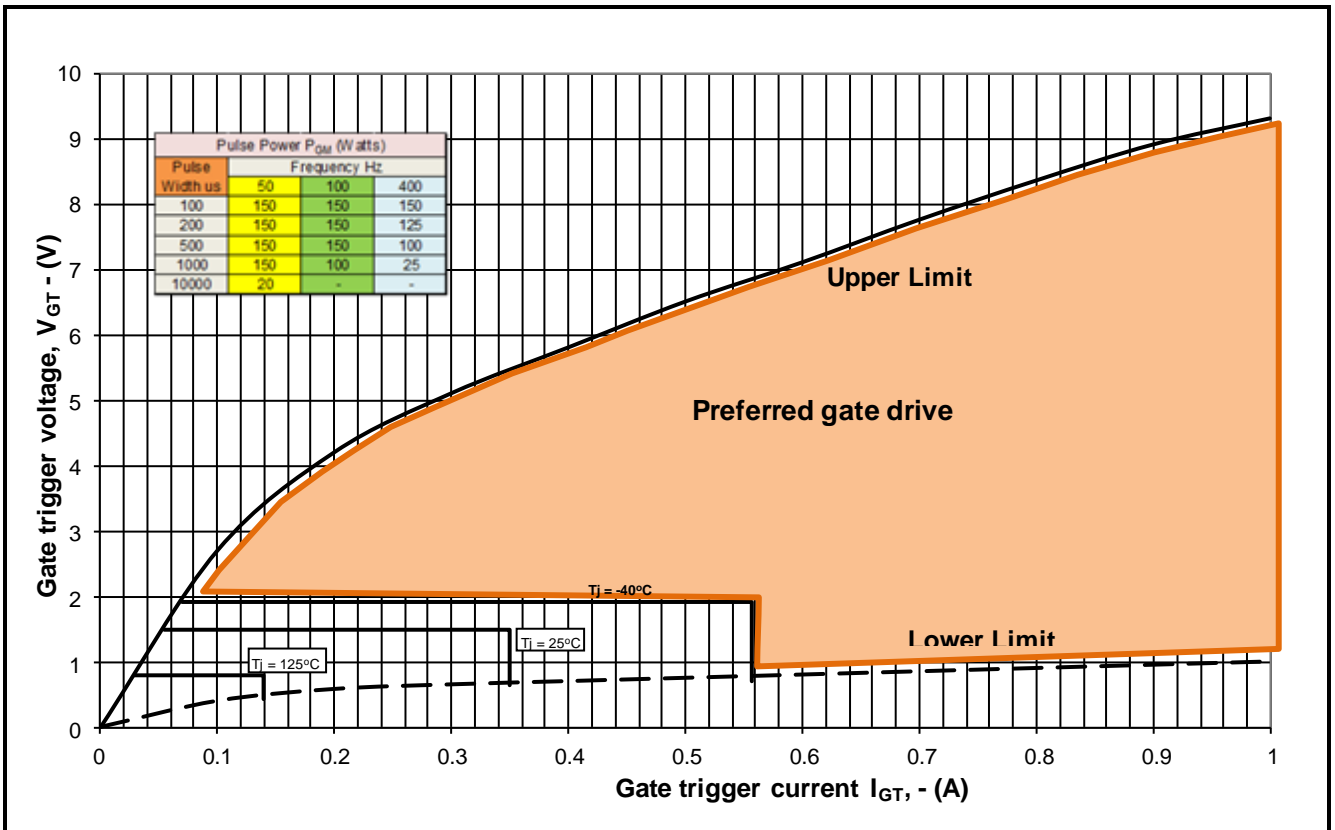


Fig14 Gate Characteristics

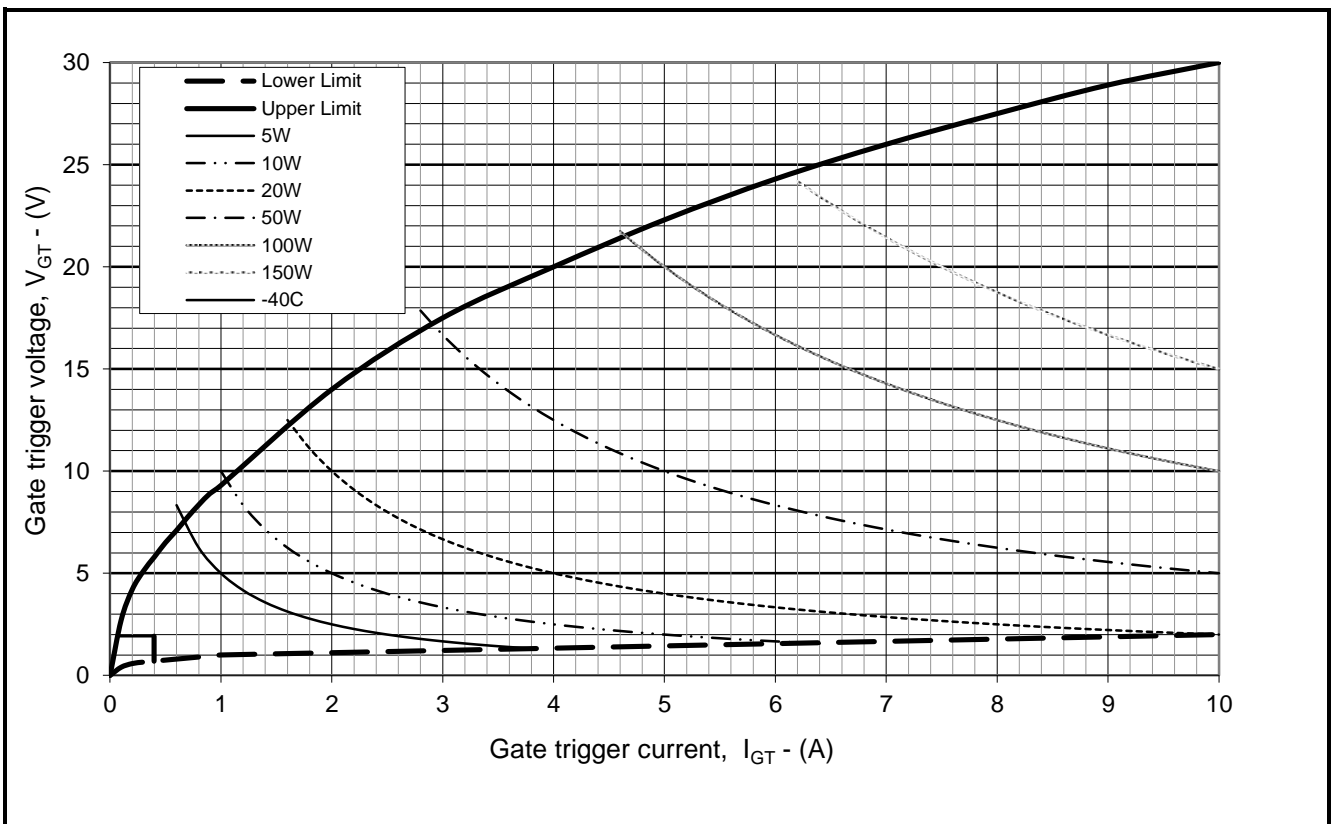
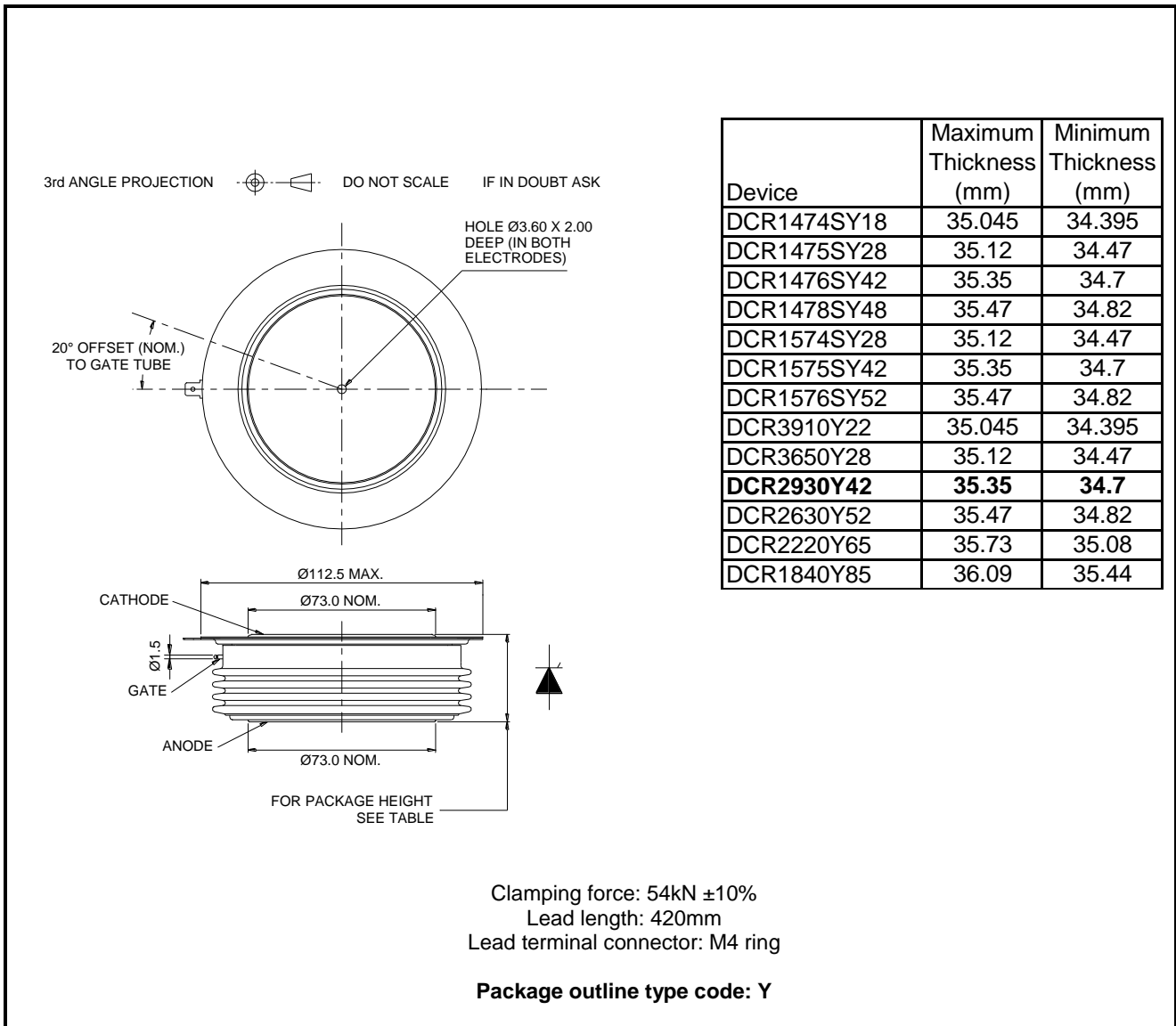


Fig. 15 Gate characteristics



**PACKAGE DETAILS**

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. **DO NOT SCALE.**



**Fig.16 Package outline**

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